Power LDMOS transistor Rev. 3 — 19 October 2020

AMPLEON

Product data sheet

Product profile 1.

1.1 General description

Based on Advanced Rugged Technology (ART) a 2000 W LDMOS power transistor for ISM application has been designed. This unmatched device covers a frequency range of 1 MHz to 450 MHz.

Table 1. **Application information**

Test signal	f	V _{DS}	PL	Gp	ηD
	(MHz)	(V)	(W)	(dB)	(%)
CW	41	65	1600	28.8	79.4
CW pulsed [1][2]	60	55	1250	24.7	85.8
CW pulsed [1][2]	60	65	1690	25.1	83.3
CW pulsed [1][2]	64	65	1785	25.7	84.7
CW [3]	87.5 to 108	60	1730	25.8	85.1

^[1] $t_p = 100 \ \mu s; \ \delta = 10 \ \%.$

1.2 Features and benefits

- High breakdown voltage enables class E operation up to V_{DS} = 50 V
- Qualified up to a maximum of V_{DS} = 65 V
- Characterized from 30 V to 65 V for extended power range
- Easy power control
- Integrated dual sided ESD protection enables class C operation and complete switch off of the transistor
- Excellent ruggedness with no device degradation
- High efficiency
- Excellent thermal stability
- Designed for broadband operation
- For RoHS compliance see the product details on the Ampleon website

^[2] Performance at 3 dB gain compression level.

^[3] Center band performance numbers across the indicated frequency range.

1.3 Applications

- Industrial, scientific and medical applications
 - Plasma generators
 - MRI systems
 - ◆ CO₂ lasers
 - ◆ Particle accelerators
- Broadcast
 - FM radio
 - ♦ VHF TV
- Communications
 - ◆ Non cellular communications
 - ◆ UHF radar

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
ART2	KOPE (OMP-1230-4F-1)		
1	gate1		_
2	gate2	4 3	4
3	drain2		1_
4	drain1		5
5	source [1]		2—
		1 2	' <u></u>
			атр01358
ART2	L 2K0PEG (OMP-1230-4G-1)	
1	gate1		
2	gate2	4 3	4
3	drain2		1
4	drain1	<u></u>	5
5	source [1]	1 2	2—
			' <u></u>
			3 amp01358

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC	Packing description	Min. orderable quantity (pieces)
OMP-1230-4F-1	ART2K0PEZ	9349 602 79517	Tray; 20-fold; dry pack	60
	ART2K0PEY	9349 602 79518	TR13; 100-fold; 56 mm; dry pack	100
OMP-1230-4G-1	ART2K0PEGZ	9349 602 78517	Tray; 20-fold; dry pack	60
	ART2K0PEGY	9349 602 78518	TR13; 100-fold; 56 mm; dry pack	100

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	<u>[1]</u>	-	200	V
V_{GS}	gate-source voltage		-6	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[2]	-	225	°C

^[1] Specified over lifetime at maximum operating temperature.

5. Thermal characteristics

Table 5. Thermal characteristics

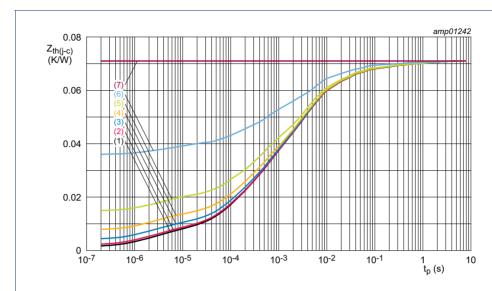
Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _j = 150 °C	[1][2]	0.071	K/W
Z _{th(j-c)}	transient thermal impedance from junction to case	$T_j = 150 ^{\circ}\text{C}; t_p = 100 \mu\text{s}; \\ \delta = 10 \%$		0.02	K/W

^[1] T_j is the junction temperature.

^[2] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

^[2] R_{th(j-c)} is measured under RF conditions.

^[3] See Figure 1.



- (1) $\delta = 1 \%$
- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 5.5 \text{ mA}$	203	208	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 20 \text{ V}; I_D = 550 \text{ mA}$	1.5	2.1	2.5	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 65 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 20 \text{ V}$	-	72.5	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 19.25 \text{ A}$	-	0.110	-	Ω

Table 7. AC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	3.27	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	614	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	187	-	pF

ART2K0PE_ART2K0PEG

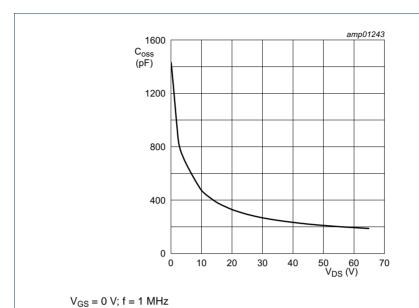


Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

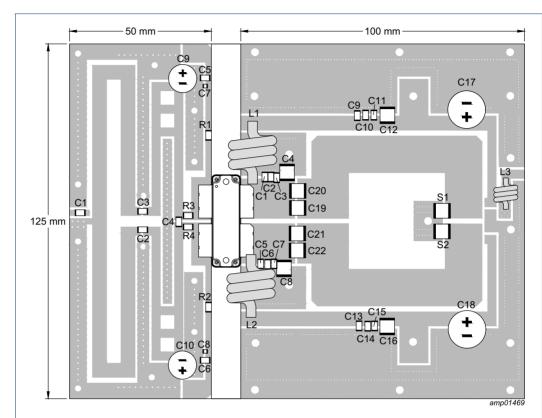
Table 8. RF characteristics

Test signal: pulsed RF; t_p = 100 μ s; δ = 3 %; f = 108 MHz; RF performance at V_{DS} = 65 V; I_{Dq} = 50 mA per section; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 2000 W	26.0	26.9	-	dB
RLin	input return loss	P _L = 2000 W	-	-15.8	-	dB
η_{D}	drain efficiency	P _L = 2000 W	68.0	71.3	-	%

7. Application information

7.1 Application circuit f = 41 MHz



Printed-Circuit Board (PCB): Rogers RO4350 double sided; ϵ_{r} = 3.5 F/m; thickness = 0.76 mm; thickness copper = 70 μ m.

See Table 9 for a list of components.

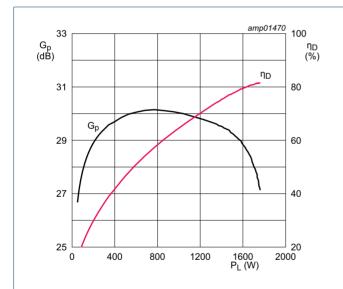
Fig 3. Component layout

Table 9. List of components For test circuit see Figure 3.

Component	Description	Value	Remarks
Output board			
C1, C2	multilayer ceramic chip capacitor	47 pF	ATC 800B
C3	multilayer ceramic chip capacitor	82 pF	ATC 800B
C4	multilayer ceramic chip capacitor	220 pF	PPI 2225
C5, C6	multilayer ceramic chip capacitor	47 pF	ATC 800B
C7	multilayer ceramic chip capacitor	82 pF	ATC 800B
C8	multilayer ceramic chip capacitor	220 pF	PPI 2225
C9, C10, C13, C14	multilayer ceramic chip capacitor	510 pF	ATC 100B
C11, C15	multilayer ceramic chip capacitor	100 nF, 100 V	TDK
C12, C16	multilayer ceramic chip capacitor	4.7 μF, 100 V	TDK
C17, C18	electrolytic capacitor	1000 μF, 100 V	

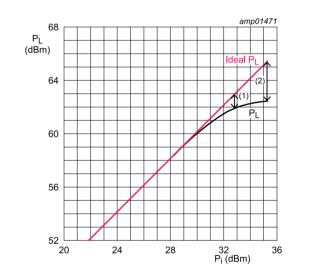
Table 9. List of components ...continued For test circuit see Figure 3.

Component	Description	Value	Remarks
C19, C20	multilayer ceramic chip capacitor	680 pF	PPI 2225
C21, C22	multilayer ceramic chip capacitor	680 pF	PPI 2225
S1, S2	copper foil	short	
L1, L2	air inductor	6 turns, d = 6 mm	1.6 mm copper wire
L3	inductor	66 nH	Coilcraft: 1212VS-66NME
Input board			
C1	multilayer ceramic chip capacitor	560 pF	ATC 100B
C2, C3	multilayer ceramic chip capacitor	470 pF	ATC 100B
C4	multilayer ceramic chip capacitor	220 pF	ATC 100B
C5, C6	multilayer ceramic chip capacitor	100 nF	TDK
C7, C8	multilayer ceramic chip capacitor	1 nF	ATC 100B
C9, C10	electrolytic capacitor	100 μF, 63 V	
R1, R2	resistor	47 Ω	SMD 1206
R3, R4	resistor	3.3 Ω	SMD 1206



 V_{DS} = 65 V; I_{Dq} = 150 mA per section; f = 41 MHz.

Fig 4. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 65 \text{ V}$; $I_{Dq} = 150 \text{ mA per section}$; f = 41 MHz.

- (1) $P_{L(1dB)} = 61.88 \text{ dBm } (1542 \text{ W})$
- (2) $P_{L(3dB)} = 62.46 \text{ dBm } (1762 \text{ W})$

Fig 5. Output power as a function of input power; typical values

8. Test information

8.1 Ruggedness in class-AB operation

The ART2K0PE and ART2K0PEG are capable of withstanding a load mismatch corresponding to VSWR ≥ 65 : 1 through all phases under the following conditions: $V_{DS} = 65$ V; $I_{Dq} = 100$ mA per section; $P_L = 2000$ W pulsed; $t_p = 100$ $\mu s; \, \delta = 10$ %; f = 108 MHz.

8.2 Impedance information

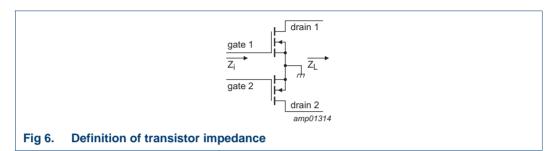


Table 10. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 65 \text{ V}$ and $P_L = 2000 \text{ W}$.

f	Z_i	Z_L
(MHz)	(Ω)	(Ω)
108	2.4 – j8.7	3.8 + j0.9

8.3 Test circuit

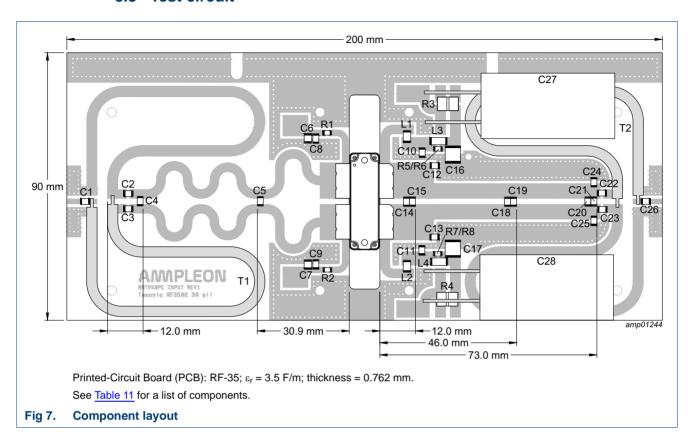


Table 11. List of components

For test circuit see Figure 7.

Component	Description	Value	Remarks
C1, C26	multilayer ceramic chip capacitor	470 pF	1
C2, C3	multilayer ceramic chip capacitor	68 pF L	1
C4	multilayer ceramic chip capacitor	43 pF	1
C5	multilayer ceramic chip capacitor	300 pF	1
C6, C7	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata: GRM32ER71H475KA88L
C8, C9, C10, C11	multilayer ceramic chip capacitor	920 pF	1
C12, C13	multilayer ceramic chip capacitor	180 pF	1
C14, C15	multilayer ceramic chip capacitor	39 pF	1
C16, C17	multilayer ceramic chip capacitor	4.7 μF, 100 V	TDK: C5750X7R2A475KT/A
C18, C19	multilayer ceramic chip capacitor	56 pF L	1
C20, C21	multilayer ceramic chip capacitor	51 pF	1
C22, C23	multilayer ceramic chip capacitor	120 pF	1
C24, C25	multilayer ceramic chip capacitor	20 pF	1
C27, C28	electrolytic capacitor	2200 μF, 100 V	
L1, L2	air inductor	47 nH	Coilcraft: 1515SQ-47N
L3, L4	air inductor	82 nH	Coilcraft: 1515SQ-82N
R1, R2	resistor	4.7 kΩ	SMD 1206

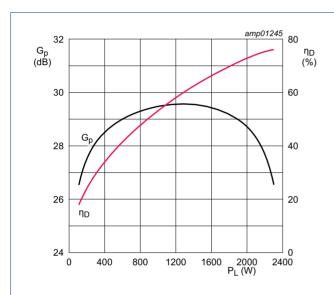
Table 11. List of components ... continued

For test circuit see Figure 7.

Component	Description	Value	Remarks
R3, R4	resistor	0.01 Ω	Vishay: WSHP2818
R5, R6, R7, R8	resistor	9.1 Ω	SMD 1206
T1, T2	semi rigid coax	50 Ω, 160 mm	EZ141-AL-TP/M17

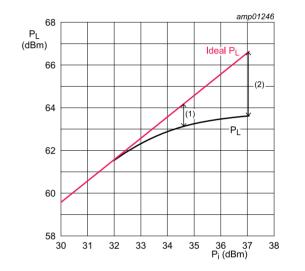
^[1] American Technical Ceramics type 100B or capacitor of same quality.

8.4 Graphical data



 V_{DS} = 65 V; I_{Dq} = 100 mA per section; f = 108 MHz; t_{D} = 100 μ s; δ = 10 %.

Fig 8. Power gain and drain efficiency as function of output power; typical values

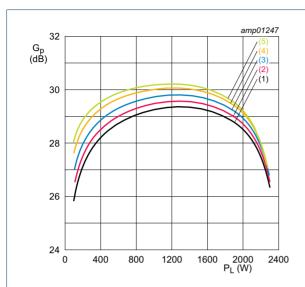


 V_{DS} = 65 V; I_{Dq} = 100 mA per section; f = 108 MHz; t_p = 100 $\mu s; \, \delta$ = 10 %.

- (1) $P_{L(1dB)} = 63.20 \text{ dBm } (2045 \text{ W})$
- (2) $P_{L(3dB)} = 63.71 \text{ dBm } (2300 \text{ W})$

Fig 9. Output power as a function of input power; typical values

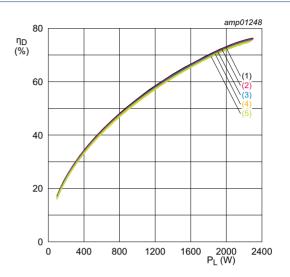
Power LDMOS transistor



 $V_{DS} = 65 \text{ V; } f = 108 \text{ MHz; } t_p = 100 \text{ } \mu\text{s; } \delta = 10 \text{ } \%.$

- (1) $I_{Dq} = 50 \text{ mA per section}$
- (2) $I_{Da} = 100 \text{ mA per section}$
- (3) $I_{Dq} = 200 \text{ mA per section}$
- (4) $I_{Dq} = 400 \text{ mA per section}$
- (5) $I_{Dq} = 600 \text{ mA per section}$

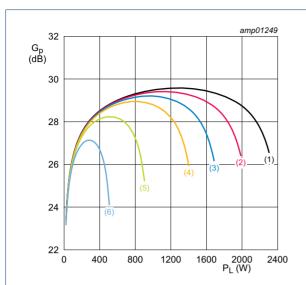
Fig 10. Power gain as a function of output power; typical values



 V_{DS} = 65 V; f = 108 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $I_{Dq} = 50 \text{ mA per section}$
- (2) $I_{Dq} = 100 \text{ mA per section}$
- (3) $I_{Dq} = 200 \text{ mA per section}$
- (4) $I_{Dq} = 400 \text{ mA per section}$
- (5) $I_{Dq} = 600 \text{ mA per section}$

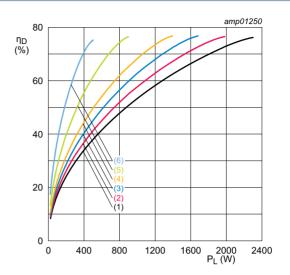
Fig 11. Drain efficiency as a function of output power; typical values



 I_{Dq} = 100 mA per section; f = 108 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $V_{DS} = 65 \text{ V}$
- (2) $V_{DS} = 60 \text{ V}$
- (3) $V_{DS} = 55 \text{ V}$
- (4) $V_{DS} = 50 \text{ V}$
- (5) $V_{DS} = 40 \text{ V}$
- (6) $V_{DS} = 30 \text{ V}$

Fig 12. Power gain as a function of output power; typical values



 I_{Dq} = 100 mA per section; f = 108 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $V_{DS} = 65 \text{ V}$
- (2) $V_{DS} = 60 \text{ V}$
- (3) $V_{DS} = 55 \text{ V}$
- (4) $V_{DS} = 50 \text{ V}$
- (5) $V_{DS} = 40 \text{ V}$
- (6) $V_{DS} = 30 \text{ V}$

Fig 13. Drain efficiency as a function of output power; typical values

9. Package outline

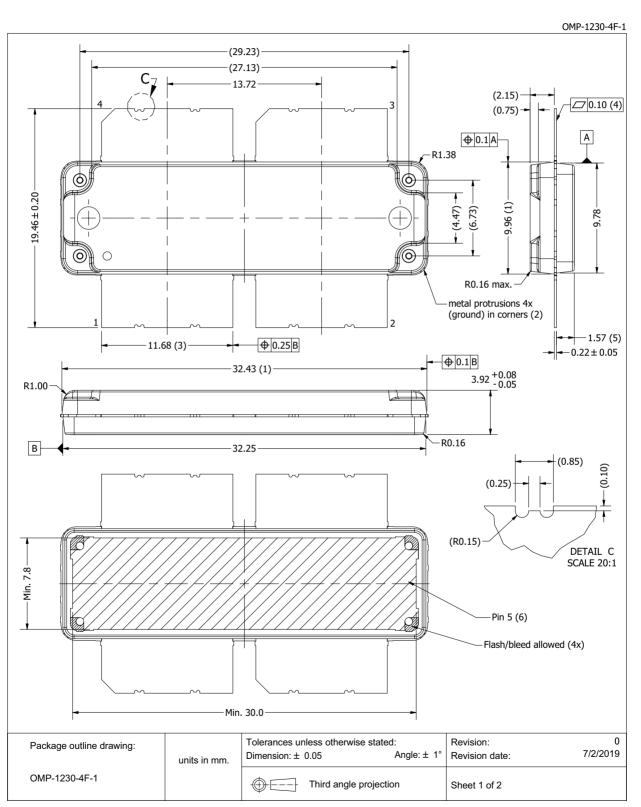
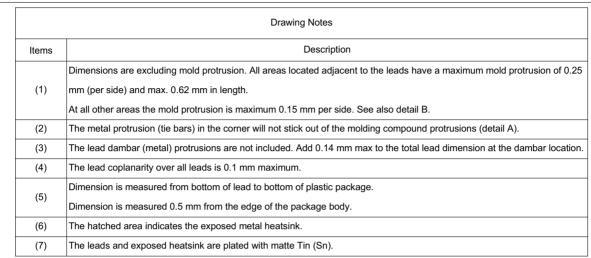


Fig 14. Package outline OMP-1230-4F-1 (sheet 1 of 2)

OMP-1230-4F-1



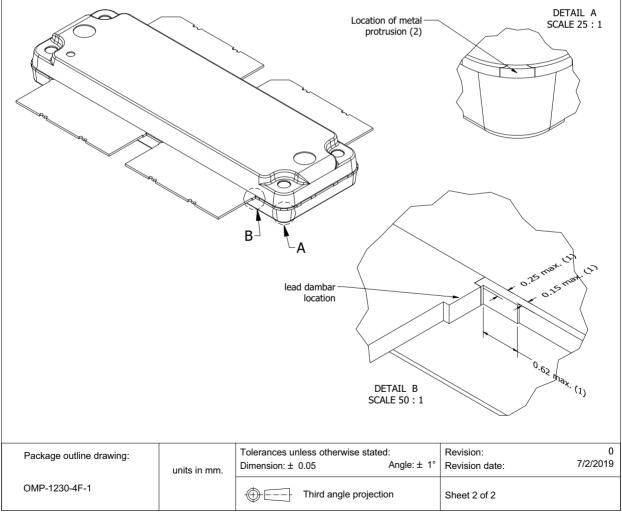


Fig 15. Package outline OMP-1230-4F-1 (sheet 2 of 2)

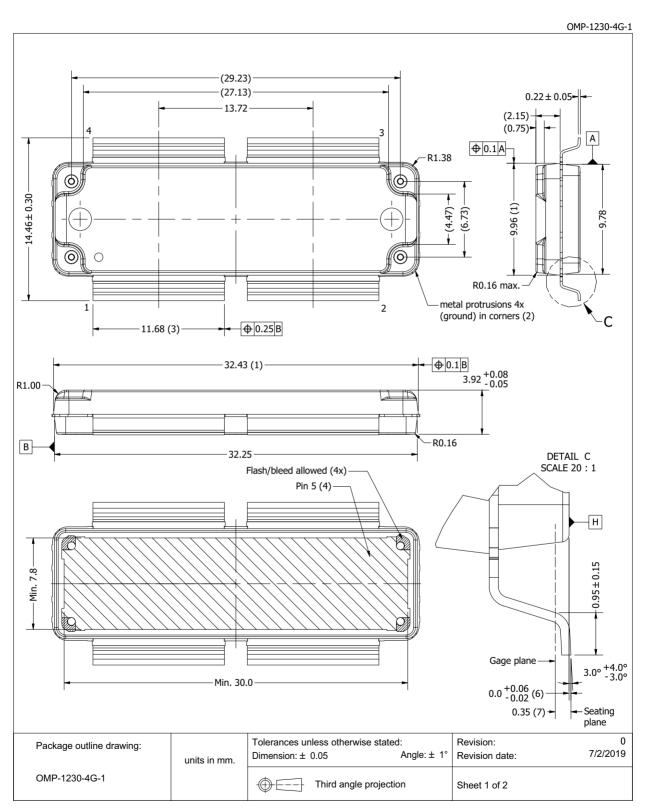


Fig 16. Package outline OMP-1230-4G-1 (sheet 1 of 2)

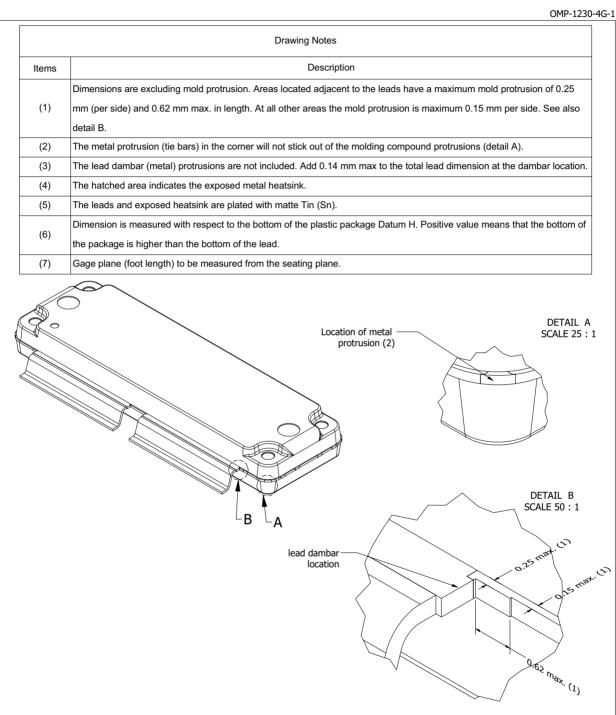


Fig 17. Package outline OMP-1230-4G-1 (sheet 2 of 2)

units in mm.

Package outline drawing:

OMP-1230-4G-1

ART2K0PE_ART2K0PEG

Tolerances unless otherwise stated:

Third angle projection

Revision:

Revision date:

Sheet 2 of 2

Angle: ± 1°

Dimension: ± 0.05

0

7/2/2019

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

11. Abbreviations

Table 13. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
FM	Frequency Modulation
ISM	Industrial, Scientific and Medical
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MRI	Magnetic Resonance Imaging
MTF	Median Time to Failure
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
UHF	Ultra High Frequency
VHF	Very High Frequency
VSWR	Voltage Standing Wave Ratio

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12. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
ART2K0PE_ART2K0PEG v.3	20201019	Product data sheet	-	ART2K0PE v.2	
Modifications:	The document now describes the straight lead and gull wing version of this product				
	Section 2 o	n page 2: added ART2K	0PEG data		
	Section 3 o	n page 3: added ART2K	0PEG data		
	Section 8.1	on page 8: added ART2	K0PEG to text		
	Section 9 o	<mark>n page 13</mark> : added packa	ge outline version	OMP-1230-4G-1	
ART2K0PE v.2	20200806	Product data sheet	-	ART2K0PE_ART2K0PEG v.1	
ART2K0PE_ART2K0PEG v.1	20200114	Objective data sheet	-	-	

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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ART2K0PE ART2K0PEG

Power LDMOS transistor

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Power LDMOS transistor

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